L Number	Hits	Search Text	DB	Time stamp
16	1623	(si or silicon) near2 single near2 crystal$5 near2 (substrate or wafer) near5 insulat$5	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/11 11:46
17	854	(si or silicon) near2 single near2 crystal$5 near2 (substrate or wafer) near5 insulat$5 and @py<1999	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/11 11:46
18	82	(si or silicon) near2 single near2 crystal$5 near2 (substrate or wafer) near5 insulat$5 and @py<1999 and 117/$.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/11 11:52
19	1	(tft or thin near2 film near2 transistor) same (sige or silicon near2 germanium) near4 grad$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/11 11:54
20	66	(sige or silicon near2 germanium) near4 grad$4 same insulat$5	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/11 11:54
21	11	(sige or silicon near2 germanium) near4 grad$4 near10 insulat$5	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/11 11:56
22	151	(sige or silicon near2 germanium) near4 grad$4 same relax$5	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/11 11:56
23	29	(sige or silicon near2 germanium) near4 grad$4 same electrode	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/11 11:58
24	604	(sige or silicon near2 germanium) near16 ion near2 implant$5	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/11 11:58
25	65	(sige or silicon near2 germanium) near16 ion near2 implant$5 near10 concentrat$5	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/11 12:40
26	41	(sige or silicon near2 germanium) near16 ion near2 implant$5 near5 (ge or germanium) near10 concentrat$5	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/11 12:52
27	345	heterojunction near2 bipolar near2 transistor same (silicon or si) near2 substrate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/11 12:53
28	92	heterojunction near2 bipolar near2 transistor same (silicon or si) near2 substrate same (sige or silicon near2 germanium)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/11 12:53
29	5	heterojunction near2 bipolar near2 transistor same (silicon or si) near2 substrate near5 insulat$5 same (sige or silicon near2 germanium)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/11 12:55

30	0	heterojunction near2 bipolar near2 transistor same (quartz) near2 substrate same (sige or silicon near2 germanium)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/11 12:55
31	0	heterojunction near2 bipolar near2 transistor same (quartz) near2 substrate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/11 12:55
32	216	heterojunction near2 bipolar near2 transistor same insulat$4 near2 substrate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/11 12:58
33	520	(thin near2 film near2 transistor or tft) same (sige or silicon near2 germanium)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/11 12:59
34	25	(thin near2 film near2 transistor or tft) same (sige or silicon near2 germanium) near10 (anneal$4 or heat near2 treat$4 or laser)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/11 13:02
35	1	(thin near2 film near2 transistor or tft) same (sige or silicon near2 germanium) near10 grad$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/11 13:00
36	11	(thin near2 film near2 transistor or tft) same (sige or silicon near2 germanium) near10 combin$6	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/11 13:03
37	662	amorphous near2 (silicon or si) same amorphous near5 (sige or silicon adj germanium) same (crystal$5 or crystalliz$4 or recrystal$4 or recrystalliz$4)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/11 13:04
38	72	amorphous near2 (silicon or si) same amorphous near5 (sige or silicon adj germanium) same (crystal$5 or crystalliz$4 or recrystal$4 or recrystalliz$4) near10 (laser or heat near2 treat$4 or anneal$4)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/11 13:16
39	142	(thin near2 film near2 transistor or tft) same (low near2 carrier near2 mobility)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/11 13:16
40	1	(thin near2 film near2 transistor or tft) same (low near2 carrier near2 mobility) same (sige or silicon near2 germanium)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/11 13:17
41	142	(thin near2 film near2 transistor or tft) same (low near2 carrier near2 mobility)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/11 13:17
42	74	(thin near2 film near2 transistor or tft) same (low near2 carrier near2 mobility) and @py<2002	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/11 13:20
43	33	(thin near2 film near2 transistor or tft) same (carrier near2 mobility) near10 "100" and @py<2002	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/11 13:37

44	1165	polysilicon near2 insulator	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/11 13:37
45	228	polysilicon adj insulator	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/11 13:55
46	23	(silicon adj germanium or sige) near10 promot$5 near2 (crystal$6 or crystalliz$4 or recrystal$5 or recrystalliz$4)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/11 14:01
47	0	(silicon adj germanium or sige) near10 (si or silicon) near4 amporphous near20 (anneal$4 or heat near2 treat$4 or rapid near2 thermal or laser)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/11 14:02
48	58	(silicon adj germanium or sige) near10 (si or silicon) near4 amporphous near20 (anneal$4 or heat near2 treat$4 or rapid near2 thermal or laser)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/11 15:31
49	274	(noguchi near2 shigeru).in.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/11 15:32
50	10	(noguchi near2 shigeru).in. and (sige or silicon adj germanium)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/11 15:32